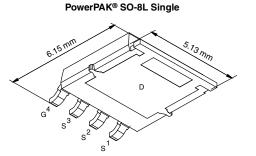


Vishay Siliconix

Automotive P-Channel 30 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY	
V _{DS} (V)	- 30
$R_{DS(on)}(\Omega)$ at V_{GS} = - 10 V	0.0085
$R_{DS(on)} (\Omega)$ at $V_{GS} = -4.5 V$	0.0200
I _D (A)	- 30 ^a
Configuration	Single



FEATURES

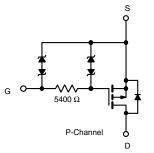
- TrenchFET[®] Power MOSFET
- ESD Protection: 3000 V
- AEC-Q101 Qualified^d
- 100 % $\rm R_g$ and UIS Tested

www.vishay.com/doc?99912

 Material categorization: For definitions of compliance please see



ROHS COMPLIANT HALOGEN



ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and Halogen-free	SQJ403EEP-T1-GE3

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unles	s otherwise noted	I)	
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	- 30	V
Gate-Source Voltage		V _{GS}	± 20	v
Continuous Drain Current ^a	T _C = 25 °C		- 30	
Continuous Drain Current-	T _C = 125 °C	Ι _D	- 30	
Continuous Source Current (Diode Conduction) ^a		I _S	- 30	А
Pulsed Drain Current ^b		I _{DM}	- 84	
Single Pulse Avalanche Current		I _{AS}	- 50	
Single Pulse Avalanche Energy L = 0.1 mH		E _{AS}	125	mJ
Maximum Dawar Disaination ^b	T _C = 25 °C	P	68	W
Maximum Power Dissipation ^b	T _C = 125 °C	P _D	22	vv
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to + 175	°C
Soldering Recommendations (Peak Temperature) ^{e, f}			260	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	68	°C/W
Junction-to-Case (Drain)		R _{thJC}	2.2	C/W

Notes

a. Package limited.

- b. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- c. When mounted on 1" square PCB (FR-4 material).

- e. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SO-8L. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- f. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

d. Parametric verification ongoing.

www.vishay.com

SQJ403EEP

Vishay Siliconix

PARAMETER	SYMBOL	TES	TEST CONDITIONS		TYP.	MAX.	UNIT
Static					•		
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} =	0 V, I _D = - 250 μA	- 30	-	-	v
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_{D} = -250 \ \mu A$		- 2.0	- 2.5	V
		V _{DS} =	$V_{DS} = 0 V, V_{GS} = \pm 12 V$		-	± 2	μA
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	± 1	mA
		$V_{GS} = 0 V$	V _{DS} = - 30 V	-	-	- 1	μA
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = - 30V, T _J = 125 °C	-	-	- 50	
		$V_{GS} = 0 V$	V _{DS} = - 30V, T _J = 175 °C	-	-	- 250	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = - 10 V	$V_{DS} \le$ - 5 V	- 30	-	-	Α
Drain-Source On-State Resistance ^a		V _{GS} = - 10 V	I _D = - 10 A	-	0.0070	0.0085	
		V _{GS} = - 10 V	I _D = - 10 A, T _J = 125 °C	-	-	0.0130	
	R _{DS(on)}	V _{GS} = - 10 V	I _D = - 10 A, T _J = 175 °C	-	-	0.0150	Ω
		V _{GS} = - 4.5 V	I _D = - 7 A	-	0.0120	0.0200	
Forward Transconductanceb	9 _{fs}	V _{DS} =	- 10 V, I _D = - 10 A	-	32	-	S
Dynamic ^b	•				•		
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = - 15 V, f = 1 MHz	-	712	890	pF
Total Gate Charge ^c	Qg			-	75	164	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = - 10 V	V _{DS} = - 15 V, I _D = - 10 A	-	9.5	-	nC
Gate-Drain Charge ^c	Q _{gd}			-	19	-	
Gate Resistance	Rg		f = 1 MHz	2	4.3	7.5	kΩ
Turn-On Delay Time ^c	t _{d(on)}			-	38	57	
Rise Time ^c	t _r	V _{DD} =	V _{DD} = - 15 V, R _I = 1.5 Ω		82	123	ns
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong$ - 10 Å, V_{GEN} = - 10 V, R_g = 1 Ω		-	134	201	
Fall Time ^c	t _f			-	178	214	
Source-Drain Diode Ratings and Char	acteristics ^b						
Pulsed Current ^a	I _{SM}			-	-	- 84	Α
Forward Voltage	V _{SD}	I _F =	- 3 A, V _{GS} = 0 V	-	- 0.75	- 1.2	V

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

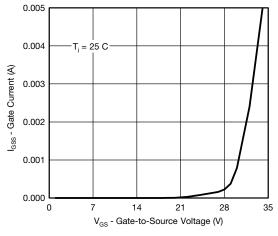
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2

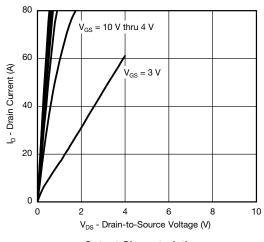


Vishay Siliconix

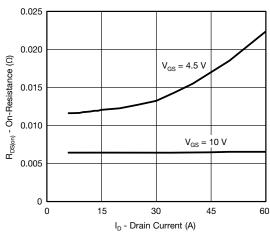
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



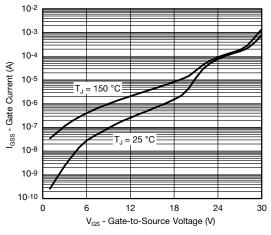
Gate Current vs. Gate-Source Voltage



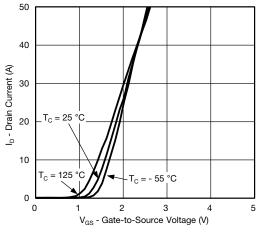




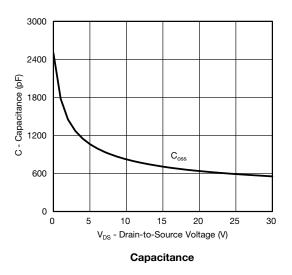
On-Resistance vs. Drain Current



Gate Current vs. Gate-Source Voltage





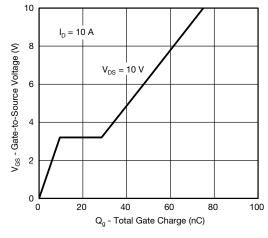


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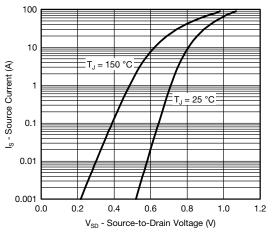


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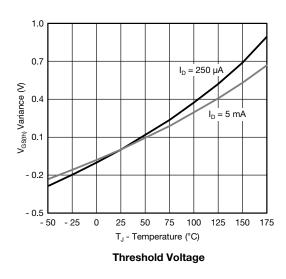
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

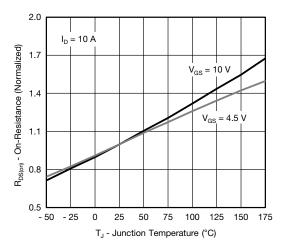


Gate Charge

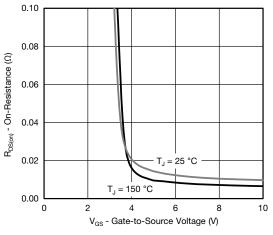


Source Drain Diode Forward Voltage

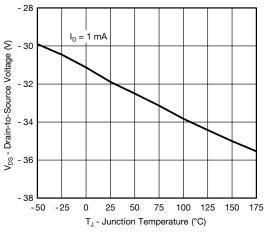




On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature

S13-0024-Rev. B, 14-Jan-13

Document Number: 67076

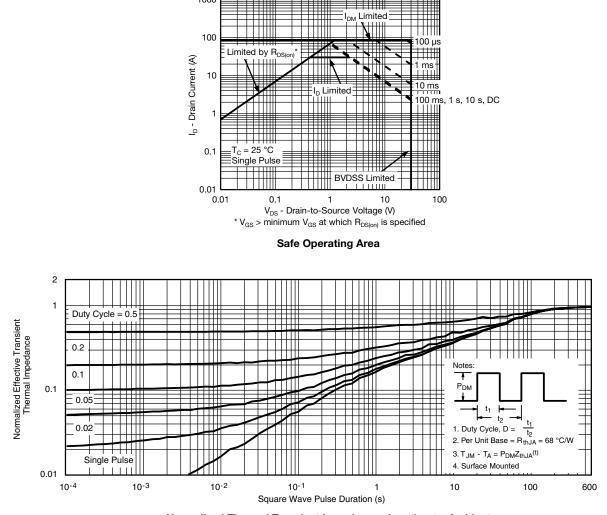
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Vishay Siliconix

THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)

1000

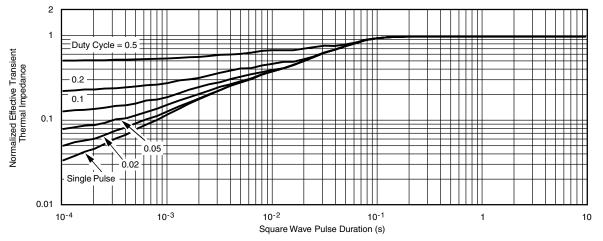


Normalized Thermal Transient Impedance, Junction-to-Ambient



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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

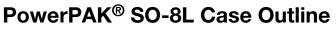
- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

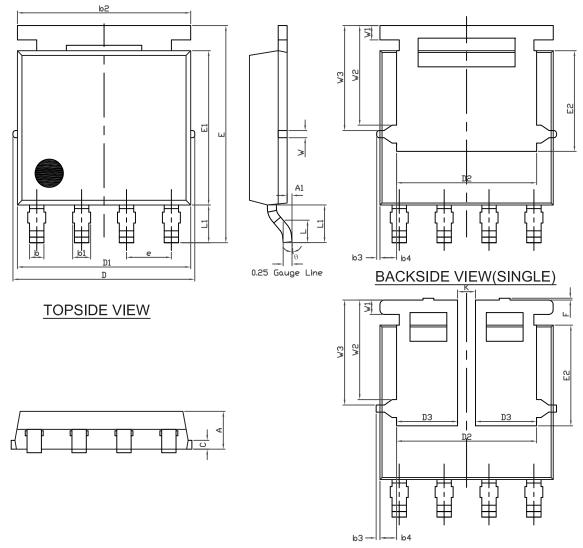
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <u>www.vishay.com/ppg?67076</u>.



Vishay Siliconix





BACKSIDE VIEW(DUAL)

Package Information



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Vishay Siliconix

DIM.	MILLIMETERS			INCHES			
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
А	1.00	1.07	1.14	0.039	0.042	0.045	
A1	0.00	-	0.127	0.00	-	0.005	
b	0.33	0.41	0.48	0.013	0.016	0.019	
b1	0.44	0.51	0.58	0.017	0.020	0.023	
b2	4.80	4.90	5.00	0.189	0.193	0.197	
b3		0.094	·		0.004		
b4		0.47			0.019		
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	5.00	5.13	5.25	0.197	0.202	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D3	1.63	1.73	1.83	0.064	0.068	0.072	
е		1.27 BSC	·	0.050 BSC			
E	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2 (for AI product)	2.75	2.85	2.95	0.108	0.112	0.116	
E2 (for other product)	3.18	3.28	3.38	0.125	0.129	0.133	
F	-	-	0.15	-	-	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
К		0.51		0.020			
W	0.23		0.009				
W1	0.41		0.016				
W2	2.82		0.111				
W3		2.96		0.117			
θ	0°	-	10°	0°	-	10°	

Note

• Millimeters will gover



Vishay Siliconix

RECOMMENDED MINIMUM PAD FOR PowerPAK[®] SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)

Revision: 07-Feb-12



Vishay

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